

SSI Solaris 100 Rapid Thermal Processing (RTP) system



RTA can be used in order to activate dopants, change film-to-film or film-to-wafer substrate interfaces, change states of grown films, repair damage from ion implantation, move dopants or drive dopants from one film into another or from a film into the wafer substrate, form ohmic contact metallization for HBT, MESFET, HEMT, Solar Cell, LED, Sensors. It can be reached to maximum temperature of 1200°C in seconds.

Specification

- Steady State Temperature range from Room to 1200°C
- Steady State Process time from 0.1 sec to unlimited time.
- Temperature accuracy & Stability of +/- 2.5°C
- Ramp Rate up to 150°C/sec
- High Accuracy K type thermo-Couple
- Wafer diameter Sizes from Small pieces to 100mm
- Three Zone Temperature Control
- MFC Controlled gas Lines